Amendments to the Claims

This listing of claims will replace all prior versions, and listing, of claims in the application.

Listing of Claims:

1. (Currently Amended) A semiconductor laser device employed in an optical pickup of a 3-beam method that divides one laser beam into three beams by an optical system, said three beams being a 0th-order beam and ± first order beams, and directs the three beams towards an optical recording medium to detect information recorded on said recording medium and detecting tracking error information during said detection by the 0th-order beam and ± first order beams reflected from said recording medium, wherein said optical system comprises:

a header portion, said header portion including a mount surface and a leading edge plane that crosses a plane defined by the mount surface;

a laser chip for generating the said one laser beam, the laser chip being mounted to the mount surface of said header portion;

a reflector, the reflector being ~~wherein a reflector is~~ attached on a side beam incident region of ~~the a~~ leading end plane of ~~said a~~ header portion and being configured and arranged so as to reflect said side beam outside said optical system, where the ~~mounted with a laser chip emitting said laser beam,~~ said side beam ~~is being~~ one of two side beams generated by said reflected ± first order beam and fed back through said optical system returning towards said header portion to strike said side beam incident region; and ~~, said reflector reflecting said side beam outside said optical system~~

wherein said reflector is constituted of a material having different properties that that of

material constituting the header portion.

2. (Original) The semiconductor laser device according to claim 1, wherein said reflector is attached at the leading end plane of the header portion so that a distance between a reflecting plane of said reflector and a light emitting point at an outgoing end plane of said laser chip is at least 50 μm and not more than 150 μm.

3. (Original) The semiconductor laser device according to claim 1, wherein said reflecting plane of said reflector is tilted having an angle of at least 10 degrees with respect to a plane perpendicular to a main beam generated by said 0th-order beam and fed back through said optical system.

4. (Original) The semiconductor laser device according to claim 1, wherein said reflector has a cross section of a saw-toothed configuration, and includes an inclination plane of a plurality of steps.

5. (Currently Amended) The semiconductor laser device according to claim 1, wherein the material constituting said reflector is ~~formed of any~~ one of a synthetic resin and metal.

6. (Original) The semiconductor laser device according to claim 5, wherein said synthetic resin includes a thermosetting resin.

7. (Original) The semiconductor laser device according to claim 5, wherein said metal includes a metal of a hardness lower than the hardness of the metal forming the header portion.

8. (Original) A method of fabricating ~~a the~~ semiconductor laser device ~~recited in claim 1~~ employed in an optical pickup of a 3-beam method that divides one laser beam into three beams by an optical system, said optical system including a header portion that includes a mount surface and a leading edge plane that crosses a plane defined by the mount surface; a laser chip for generating the said one laser beam and being mounted to the mount surface of said header portion; and a reflector that is attached on a side beam incident region of the leading end plane of said header portion and being configured and arranged so as to reflect said side beam outside the optical system, where the said side beam is one of two side beams generated by said reflected ± first order beam and fed back through said optical system returning towards said header portion to strike said side beam incident region, said fabricating method comprising the steps of:

_____attaching at said side beam incident region at ~~the a~~ leading end plane of said header portion a base material of a reflector formed of a metal that is softer than the metal forming said header portion; and ~~or a synthetic resin prior to curing, and then~~

_____shaping said attached base material into a reflector of a predetermined configuration so as to reflect said side beam outside the optical system.

Claims 9-18 Canceled

19. (New) The fabricating method of claim 8, wherein said shaping includes shaping the reflector so a reflecting plane of said reflector is configured and arranged so a distance between the reflecting plane and a light emitting point at an outgoing end plane of said laser chip is at least 50 μm and not more than 150 μm.

20. (New) The fabricating method of claim 19, wherein said shaping includes shaping the reflector so the reflector plane is configured and arranged so as to be titled at an angle of at least 10 degrees with respect to a plane perpendicular to a main beam generated by said 0th-order beam.

21. (New) The fabricating method of claim 8, wherein said shaping includes shaping the reflector so as to form a plurality of inclined planes.

22. (New) A method of fabricating a semiconductor laser device employed in an optical pickup of a 3-beam method that divides one laser beam into three beams by an optical system, said optical system including a header portion that includes a mount surface and a leading edge plane that crosses a plane defined by the mount surface; a laser chip for generating the said one laser beam and being mounted to the mount surface of said header portion; and a reflector that is attached on a side beam incident region of the leading end plane of said header portion and being configured and arranged so as to reflect said side beam outside the optical system, where the said

side beam is one of two side beams generated by said reflected ± first order beam and fed back through said optical system returning towards said header portion to strike said side beam incident region, said fabricating method comprising the steps of:

attaching at said side beam incident region at the leading end plane of said header portion a base material of a reflector formed of a synthetic resin prior to curing, and ~~then~~ shaping said attached base material into a reflector of a predetermined configuration so as to reflect said side beam outside the optical system.

23. (New) The fabricating method of claim 22, wherein said shaping includes shaping the reflector so a reflecting plane of said reflector is configured and arranged so a distance between the reflecting plane and a light emitting point at an outgoing end plane of said laser chip is at least 50 μm and not more than 150 μm.

24. (New) The fabricating method of claim 23, wherein said shaping includes shaping the reflector so the reflector plane is configured and arranged so as to be titled at an angle of at least 10 degrees with respect to a plane perpendicular to a main beam generated by said 0th-order beam.

25. (New) The fabricating method of claim 22, wherein said shaping includes shaping the reflector so as to form a plurality of inclined planes.

26. (New) The semiconductor laser device of claim 1, wherein the reflector is configured and arranged so as to be smaller in dimension that said leading edge plane but sufficient to intercept and reflect the said side beam.

27. (New) The semiconductor laser device according to claim 1, wherein said material constituting the reflector is a synthetic resin and a reflective material filler.

28. (New) The semiconductor laser device according to claim 1, wherein said reflector is constituted of a reflectance- reducing material, the reflectance reducing material including one type of an epoxy resin and an UV resin and a non-reflective filler being at least one type of silica and carbon powder as a filler.